

Metal-Dimer Atomic Reconstruction Leading to Deep Donor States of the Anion Vacancy in II-VI and Chalcopyrite Semiconductors

S. J. Lee, A. D. A. Z. Lee

National Renewable Energy Laboratory, Golden, Colorado 80401, USA

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First-principles calculations reveal that the reconstruction of anion vacancies in II-VI and chalcopyrite semiconductors leads to the formation of deep donor states. The reconstruction is shown to be a metal-dimer structure, which is stable in the ground state. The formation of these states is observed in the band structure calculations for ZnSe and CdTe. The results are compared with the experimental data for ZnSe and CdTe. The results show that the reconstruction of anion vacancies in II-VI and chalcopyrite semiconductors leads to the formation of deep donor states. The reconstruction is shown to be a metal-dimer structure, which is stable in the ground state. The formation of these states is observed in the band structure calculations for ZnSe and CdTe. The results are compared with the experimental data for ZnSe and CdTe. The results show that the reconstruction of anion vacancies in II-VI and chalcopyrite semiconductors leads to the formation of deep donor states.

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Vacancies in II-VI and chalcopyrite semiconductors lead to the formation of deep donor states. The reconstruction of anion vacancies in II-VI and chalcopyrite semiconductors leads to the formation of deep donor states. The reconstruction is shown to be a metal-dimer structure, which is stable in the ground state. The formation of these states is observed in the band structure calculations for ZnSe and CdTe. The results are compared with the experimental data for ZnSe and CdTe. The results show that the reconstruction of anion vacancies in II-VI and chalcopyrite semiconductors leads to the formation of deep donor states.

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Z Se a d CuGaSe₂ [20]. T e LDA ba d a e
c ec ed b ac ed a e ca d a e

$a_1(a)$ b a
 Z Se ($CuGaSe_2$) $E_v + 1.1$ eV ($E_v + 0.2$ eV), b e
 $E_v + 0.2$ eV ($E_v - 2.5$ eV), a e e a a .
 T , a , a e d e , e a e F . 1, a e
 e a a , e d , b c c e d a_1^2 e e c a e d
 Z Se , a b e e VBM , e e a $CuGaSe_2$
 dee *inside* e a e c e b a d W e V_{Se}^0 e d c e ,
 e e a_1^0 c , a V_{Se}^{2+} (F . 1), a
 b e a , e e a - e a d e (Table I), a d a e ,
 e a T_d a c e e (F . 1, b). T e
 e - a c e e e e e a_1 a e Z Se e
up $E_v + 0.2$ eV (V_{Se}^0) $E_v + 2.5$ eV (V_{Se}^{2+}), e e a
 $CuGaSe_2$ e *up* $E_v - 2.5$ eV (V_{Se}^0) $E_v +$
 1.5 eV (V_{Se}^{2+}) [20]. T a a c e a e d
 c e e c a b e , d e e a c a
 e e c a c e e c , .e., e e e e e e c c
 C , b e , d e e a_1^2 (V_{Se}^0) \rightarrow a_1^0 (V_{Se}^{2+}) a -
, , d a e d a c e a_1 e e a d *lower*
 e e e . B e c a e e c a e a e d e d e
 e d e c e e *below* VBM *above* VBM , e
 Se a c c a c e c a a , e a e a a b e
 c , a , c e e c a e a e d
 e VBM e d e c e e , e e a e e e .
 T , e Se a c c a e a e e e e -

